

Abstract of the Disclosure

5 A laser beam processing method for a semiconductor wafer having a low-dielectric insulating film formed on the front surface of a semiconductor substrate, a plurality of circuits sectioned by streets formed in a lattice pattern, and metal patterns for testing partially formed on each street, comprising:

10 a laser beam processing step for applying a laser beam to the positions of the areas at which the metal patterns are located and the area of the low-dielectric insulating film under different processing conditions to remove the metal patterns and the low-dielectric insulating film.